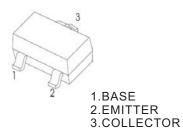


# MMBT3904 NPN TRANSISTOR



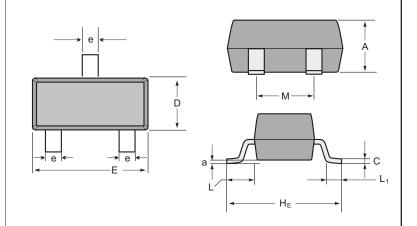
### **FEATURES**

• Complementary to MMBT3906



### Marking

Type number	Marking code
MMBT3904	1AM



#### SOT-23 mechanical data

UN	NIT.	Α	С	D	Е	HE	Ф	М	L	L <sub>1</sub>	а																									
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55	0.55	0.55	0.55	0.55	0.55	0.55	0.55	0.55	0.55	0.55	0.55	0.55	0.55	0.55	0.55	0.55	0.55	0.55	0.55	0.55	0.55	0.55	0.55	0.55	0.55	0.36	0.0
mm	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7	(ref)	(ref)	0.15																									
mil	max	43	6	55	118	102	20	77	22 (ref)		0.0																									
'''''	min	35	3	47	110	87	12	67		(ref)	6																									

# MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	Vсво	60	V
Collector-Emitter Voltage	Vceo	40	V
Emitter-Base Voltage	VEBO	6	<b>V</b>
Collector Current — Continuous	Ic	200	mA
Collector Power Dissipation	Pc	200	mW
Thermal Resistance From Junction To Ambient	RthJA	625	°C/W
Operation Junction and Storage Temperature Range	TJ,Tstg	-55~+150	ů

## MMBT3904

### **CLASSIFICATION OF hfe**

HFE	100-300				
Rank	L	Н			
Range	100-200	200-300			

## ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted.)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	Ic = 10uA, IE = 0	60			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	Ic = 1 mA, I <sub>B</sub> = 0	40			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	IE = 10uA, Ic = 0	6			V
Collector cut-off current	Icex	VCE = 30V, VBE(off) = 3V			50	nA
Collector cut-off current	Ісво	V <sub>CB</sub> = 60V, I <sub>E</sub> = 0			100	nA
Emitter cut-off current	ІЕВО	V <sub>EB</sub> = 5V, I <sub>C</sub> =0			100	nA
DC current gain	h <sub>FE1</sub>	VcE = 1V, Ic=10mA	100		300	
	h <sub>FE2</sub>	VcE = 1V, Ic = 50mA	60			
	h <sub>FE3</sub>	VcE = 1V, Ic = 100mA	30			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	Ic = 50mA, IB = 5mA			0.3	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	Ic = 50mA, IB = 5mA			0.95	V
Transition frequency	f⊤	VcE = 20V, Ic = 10mA, f=100MHz	300			MHZ
Delay time	td	Vcc=3V,VBE(off)=-0.5V			35	ns
Rise time	tr	Ic=10mA,I <sub>B1</sub> =1mA			35	ns
Storage time	ts	Vcc = 3V, Ic = 10mA			200	ns
Fall time	tf	IB1=IB2=1mA			50	ns

### RATING AND CHARACTERISTIC CURVES (MMBT3904)

